



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tomoyoshi KUSHIDA

Group Art Unit: 2811

Application No.: 09/435,766

Examiner: S. Loke

Filed: November 8, 1999

Docket No.: 104361

For: SEMICONDUCTOR DEVICE

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the June 3, 2002 Office Action, and the interview held September 24, 2002, the period for reply extended to October 3, 2002, by a Petition for Extension of Time filed herewith, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 12 and 28-30 as follows:

12. (Five Times Amended) A semiconductor device comprising:
- a substrate having a first conductive type;
  - a drift region having the first conductive type and disposed on the substrate;
  - a channel region having a second conductive type different from the first conductive type and provided on the drift region;
  - a gate region provided so as to surround at least the channel region via an insulation film; and
  - a source region having the first conductive type and provided on the channel region, the source region is located substantially at a center of the channel region, wherein an impurity concentration of the channel region is <sup>1121st</sup>equal to or less than an impurity concentration in the drift region, and <sup>1121st</sup>a depletion layer forms over the entire channel region sandwiched between the gate region when a zero bias is applied to the gate region.

22/F  
FJONES  
10-11-02

RECEIVED  
OCT - 8 2002  
TECHNOLOGY CENTER 2800

Sub  
G1

fig. 9B  
or fig. 10B  
with 1121st